

# RH1021-10

#### DESCRIPTION

The RH1021-10 is a precision 10V reference with ultralow drift and noise, extremely good long-term stability and almost total immunity to input voltage variations. The reference output will source and sink up to 10mA. This reference can also be used as a shunt regulator (2-terminal Zener). Unique circuit design makes the RH1021-10 the first IC reference to offer ultralow drift without the use of high power on-chip heaters.

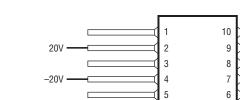
The wafer lots are processed to Linear Technology's inhouse Class S flow to yield circuits usable in stringentmilitary applications.

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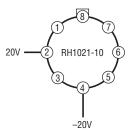
## Precision 10V Reference

#### **ABSOLUTE MAXIMUM RATINGS**

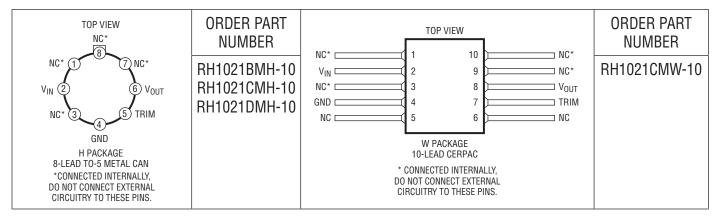
(Note 10)	
Input Voltage40	/
Input/Output Voltage Differential	/
Output to Ground Voltage	
(Shunt Mode Current Limit)16\	/
Trim Pin to Ground Voltage	
Positive Equal to V <sub>OU</sub> -	
Negative20	/
Output Short-Circuit Duration	
V <sub>IN</sub> = 35V 10 sec	3
$V_{IN} \le 20V$ Indefinite	9
Operating Temperature Range55°C to 125°C	)
Storage Temperature Range65°C to 150°C	)
Lead Temperature (Soldering, 10 sec) 300°C	)



#### **BURN-IN CIRCUITS**



#### PACKAGE/ORDER INFORMATION





### TABLE 1: ELECTRICAL CHARACTERISTICS (Preirradiation) (Note 9)

SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	A = 25° TYP	C Max	SUB- Group	–55°( Min	C ≤ T <sub>A</sub> ≤ Typ	125°C Max	SUB- Group	UNITS
V <sub>OUT</sub>	Output Voltage	RH1021CM-10 RH1021BM-10, DM-10	1 1	9.995 9.95		10.005 10.05	1					V V
TCV <sub>OUT</sub>	Output Voltage Temperature Coefficient	RH1021BM-10 RH1021CM-10, DM-10	2 2							5 20	2, 3 2, 3	ppm/°C ppm/°C
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$\begin{array}{l} 11.5V \leq V_{IN} \leq 14.5V \\ 14.5V \leq V_{IN} \leq 40V \end{array}$	3 3			4 2	1			6 4	2, 3 2, 3	ppm/V ppm/V
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation (Sourcing Current)	$0 \le I_{OUT} \le 10 \text{mA}$	3			25	1			40	2, 3	ppm/mA
	Load Regulation (Shunt Mode)	$1.7 \text{mA} \le I_{OUT} \le 10 \text{mA}$	3, 4			100	1			150	2, 3	ppm/mA
I <sub>S</sub>	Supply Current (Series Mode)					1.7	1			2.0	2, 3	mA
I <sub>MIN</sub>	Minimum Current (Shunt Mode)	V <sub>IN</sub> is Open				1.5	1			1.7	2, 3	mA
	Output Voltage Noise	$\begin{array}{l} 0.1 \text{Hz} \leq f \leq 10 \text{Hz} \\ 10 \text{Hz} \leq f \leq 1 \text{kHz} \end{array}$	5 5		6	6	4					μV <sub>P-P</sub> μV <sub>RMS</sub>
	Long-Term Stability of V <sub>OUT</sub>	∆T = 1000 Hrs Noncumulative	6		15							ppm
	Temperature Hysteresis of V <sub>OUT</sub>	$\Delta T = \pm 25^{\circ}C$			5							ppm

### TABLE 1: ELECTRICAL CHARACTERISTICS (Postirradiation) (Note 7)

				10Kr	ad(Si)	20Kr	ad(Si)	50Kr	ad(Si)	100K	rad(Si)	200K	rad(Si)	
SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNITS
V <sub>OUT</sub>	Output Voltage	RH1021CM-10 RH1021BM-10, DM-10	1 1	9.992 9.95	10.008 10.05	9.99 9.945	10.01 10.055	9.987 9.942	10.013 10.06	9.985 9.938	10.015 10.06	9.98 9.935	10.02 10.065	V V
TCV <sub>OUT</sub>	Output Voltage Temperature Coefficient	RH1021BM-10 RH1021CM-10, DM-10	2 2		5 20		5 20		5 20		7 22		10 25	ppm/°C ppm/°C
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$\begin{array}{l} 11.5V \leq V_{IN} \leq 14.5V \\ 14.5V \leq V_{IN} \leq 40V \end{array}$	3 3		4 2		4 2		4.5 2		5 2		6 3	ppm/V ppm/V
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation (Sourcing Current)	$0 \le I_{OUT} \le 10 \text{mA}$	3, 8		25		25		25		25		25	ppm/mA
	Load Regulation (Shunt Mode)	$1.7 \text{mA} \le I_{\text{OUT}} \le 10 \text{mA}$	3, 4		100		100		100		100		150	ppm/mA
I <sub>MIN</sub>	Minimum Current (Shunt Mode)	V <sub>IN</sub> is Open			1.5		1.5		1.5		1.5		1.5	mA
I <sub>S</sub>	Supply Current (Series Mode)				1.7		1.7		1.7		1.7		1.7	mA





## TABLE 1A: ELECTRICAL CHARACTERISTICS

**Note 1:** Output voltage is measured immediately after turn-on. Changes due to chip warm-up are typically less than 0.005%.

**Note 2**: Temperature coefficient is measured by dividing the change inoutput voltage over the temperature range by the change in temperature. Separate tests are done for hot and cold;  $T_{MIN}$  to 25°C and 25°C to  $T_{MAX}$ . Incremental slope is also measured at 25°C.

**Note 3:** Line and load regulation are measured on a pulse basis. Output changes due to die temperature change must be taken into account separately. Package thermal resistance is 150°C/W for the TO-5 (H) package and 170°C/W for the 10-lead flatpack (W) package.

**Note 4:** Shunt mode regulation is measured with the input open. With the input connected, shunt mode current can be reduced to OmA. Load regulation will remain the same.

**Note 5:** RMS noise is measured with a 2-pole highpass filter at 10Hz and a 2-pole lowpass filter at 1kHz. The resulting output is full wave rectified and then integrated for a fixed period, making the final reading an average as opposed to RMS. Correction factors are used to convert from average to RMS and to correct for the nonideal bandpass of the filters. Peak-to-peak noise is measured with a single highpass filter at 0.1Hz and a 2-pole lowpass filter at 10Hz. The unit is enclosed in a still-air environment to eliminate thermocouple effects on the leads. Test time is 10 seconds.

Note 6: Consult factory for units with long term stability data.

Note 7:  $V_{IN} = 15V$ ,  $I_{OUT} = 0$ ,  $T_A = 25$ °C, unless otherwise noted. Note 8:  $I_{OUT(MAX)}$  (Sourcing) is 5mA for exposures greater than 100Krad (Si).

Note 9:  $V_{IN} = 15V$ ,  $I_{OUT} = 0$ , unless otherwise noted.

**Note 10:** Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

The PDA is specified as 5% based on failures from group A, subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883. The verified failures of group A, subgroup 1, after burn-in divided by the total number of devices submitted for burn-in in

Linear Technology Corporation reserves the right to test to tighter limits

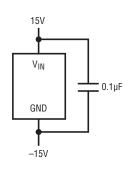
that lot shall be used to determine the percent for the lot.

### TABLE 2: ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
Final Electrical Test Requirements (Method 5004)	1*, 2, 3, 4
Group A Test Requirements (Method 5005)	1, 2, 3, 4
Group B and D for Class S and Group C and D for Class B End Point Electrical Parameters (Method 5005)	1, 2, 3

\*PDA Applies to subgroup 1. See PDA Test Notes.

## TOTAL DOSE BIAS CIRCUIT

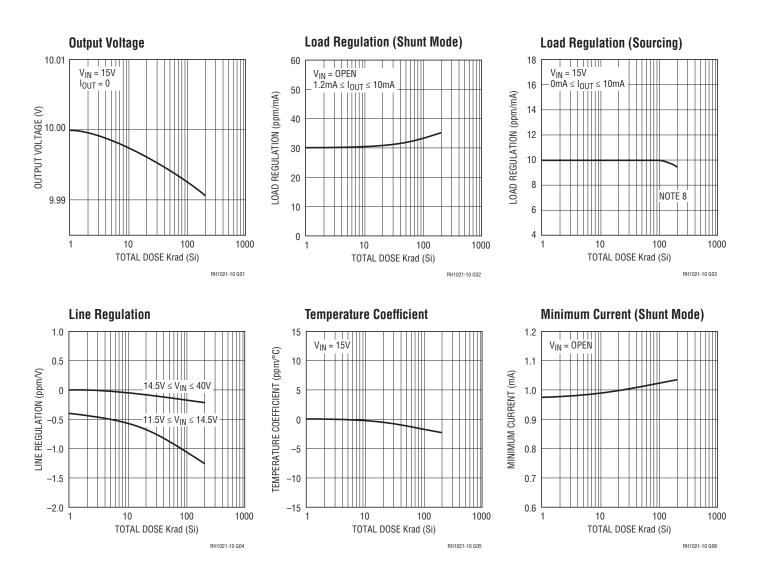


**PDA Test Notes** 

than those given.



## **TYPICAL PERFORMANCE CHARACTERISTICS**



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